### JAN/JANTX/JANTXV 4N47, 4N48, 4N49 [A]



#### Features:

- TO-78 hermetically sealed package
- High current transfer ratio
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JAN, JANTX and JANTXV devices processed to MIL-PRF-19500
- Patent No. 4124860



#### **Description:**

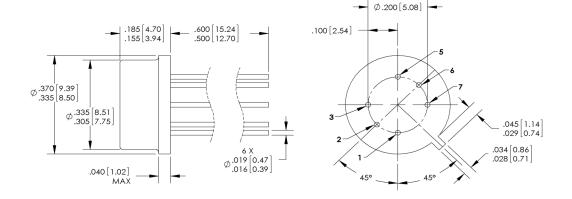
Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed TO-78 package. Devices are designed for military and/or harsh environments. The suffix letter "A" denotes the collector is electrically isolated from the case.

The JAN / JANTX / JANTXV 4N47, 4N47A, 4N48A, 4N48A, 4N49A devices are processed to MIL-PRF-19500/548. This series of 4N products are JEDEC registered, DSCC qualified.

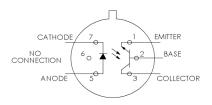
Please contact your local representative for more information.

#### **Applications:**

- High-voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment



DIMENSIONS ARE IN INCHES [MIM]



**BOTTOM VIEW** 

 Pin #
 Function
 Pin #
 Function

 3
 Collector
 5
 Anode

 2
 Base
 6
 Open

 1
 Emitter
 7
 Cathode

General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.





### **Electrical Specifications**

Absolute Maximum Ratings (T<sub>A</sub> = 25° C unless otherwise noted)

Storage Temperature Range	-55° C to +150° C
Operating Temperature Range	-55° C to +125° C
Input-to-Output Isolation Voltage	± 1.00 kVDC <sup>(1)</sup>
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(2)</sup>

#### **Input Diode**

Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Power Dissipation	60 mW <sup>(3)</sup>

#### **Output Phototransistor:**

<u> </u>	
Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Collector-Base Voltage	45 V
Emitter-Base Voltage	7.0 V
Power Dissipation	300 mW <sup>(4)</sup>

#### Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- 2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.

Ordering Information						
Part Number	Isolation I <sub>F</sub> (mA) Voltage (kV) Typ / Max		V <sub>CE</sub> (Volts) Max	Processing MIL-PRF- 195000		
JAN4N47 or JAN4N47A						
JANTX4N47 or JANTX4N47A	]					
JANTXV4N47 or JANTXV4N47A	]					
JAN4N48 or JAN4N48A	I		40	548		
JANTX4N48 or JANTX4N48A	1	1 / 40				
JANTXV4N48 or JANTXV4N4A8						
JAN4N49 or JAN4N49A	I					
JANTX4N49 or JANTX4N49A	I					
JANTXV4N49 or JANTXV4N49A						

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#### Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Dioc	le	•				
$V_{F}$	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	$I_F = 10.0 \text{ mA}$ $I_F = 10.0 \text{ mA}, T_A = -55^{\circ} \text{ C}^{(1)}$ $I_F = 10.0 \text{ mA}, T_A = 100^{\circ} \text{ C}^{(1)}$
$I_R$	Reverse Current	-	-	100	μΑ	V <sub>R</sub> = 2.0 V
Output Ph	ototransistor					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	40	-	-	V	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0, I <sub>F</sub> = 0
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	45	-	-	V	I <sub>C</sub> = 100 μA, I <sub>B</sub> = 0, I <sub>F</sub> = 0
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	7	-	-	V	I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0, I <sub>F</sub> = 0
I <sub>C(OFF)</sub> <sup>1</sup>	Collector-Emitter Dark Current	-	-	100	nA	V <sub>CE</sub> = 20 V, I <sub>B</sub> = 0, I <sub>F</sub> = 0
I <sub>C(OFF)</sub> <sup>2</sup>	Collector-Emitter Dark Current	-	-	100	μΑ	$V_{CE} = 20 \text{ V}, I_B = 0, I_F = 0, T_A = 100^{\circ} \text{ C}^{(1)}$
I <sub>CB(OFF)</sub>	Collector-Base Dark Current	-	-	10	nA	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0, I <sub>F</sub> = 0
Coupled						
	On-State Collector Current  JAN / JANTX / JANTXV 4N47 [A]	0.50 0.70 0.50	- - -	-	mA	$I_F = 1.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0$ $I_F = 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)}$ $I_F = 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)}$
I <sub>C(ON)</sub>	JAN / JANTX / JANTXV 4N48 [A]	1.00 1.40 1.00	-	5 - -		$\begin{split} I_F &= 1.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0 \\ I_F &= 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 2.0 \text{ mA, } V_{CE} = 5.0 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
	JAN / JANTX / JANTXV 4N49 [A]	2.00 2.80 2.00	- - -	10 - -		$\begin{split} I_F &= 1.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0 \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V, I}_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
I <sub>CB(ON)</sub>	On-State Collector Base	30	-	-	μΑ	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0, I <sub>F</sub> = 10 mA
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N47 [A] JAN / JANTX / JANTXV 4N48 [A] JAN / JANTX / JANTXV 4N49 [A]	- - -		0.30 0.30 0.30	V	$I_F = 2.0 \text{ mA}, I_C = 0.5 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 1.0 \text{ mA}, I_B = 0$ $I_F = 2.0 \text{ mA}, I_C = 2.0 \text{ mA}, I_B = 0$
H <sub>FE</sub>	DC Current Gain	100	-	-	V	V <sub>CE</sub> = 5.0 V , I <sub>C</sub> = 10.0 mA, I <sub>F</sub> = 0 mA
R <sub>IO</sub>	Resistance (Input-to-Output)	10 <sup>11</sup>	-	-	Ω	V <sub>I-O</sub> = ± 1000 VDC <sup>(3)</sup>
C <sub>IO</sub>	Capacitance (Input-to-Output)	-	-	5	pF	V <sub>I-O</sub> = 0 V, f = 1.0 MHz <sup>(3)</sup>
	<u> </u>			1		1

20

μs

#### Notes:

 $T_{R}, T_{F}$ 

1. Guaranteed but not tested.

Rise and Fall Time

- 2. Sample tested, LTPD = 10.
- 3. Measured with input leads shorted together and output leads shorted together.

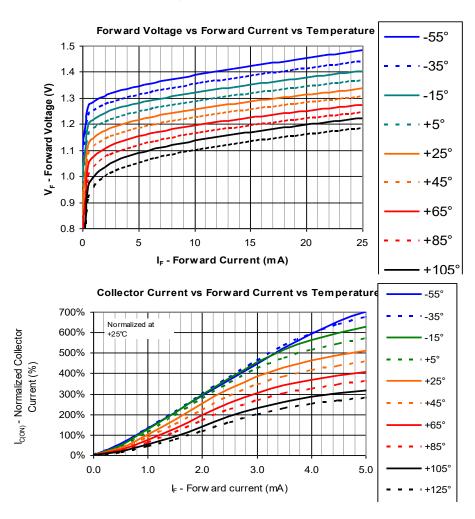
#### General Note

 $V_{CC}$  = 10.0 V ,  $I_F$  = 5.0 mA,  $R_L$  = 100  $\Omega$ 

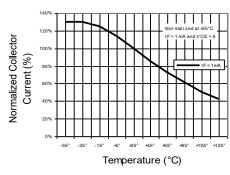
# JAN/JANTX/JANTXV 4N47, 4N48, 4N49 [A]



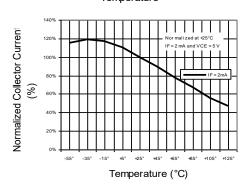
### **Typical Performance Curves**



#### Normalized Collector Current Vs Temperature



#### Normalized Collector Current Vs Temperature



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**Authorized Distributor** 

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### **TT Electronics:**

<u>JANTX4N47</u> <u>JAN4N49</u> <u>JANTX4N47A</u> <u>JANTXV4N48</u> <u>JANTX4N49</u> <u>JAN4N48A</u> <u>JANTX4N48A</u> <u>JANTX4N48A</u> <u>JANTX4N48A</u> <u>JANTX4N48A</u> <u>JANTX4N47A</u>